

Description

The AU1801P4-3D is a high power TVS, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive lines. The AU1801P4-3D complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into a 3-pin DFN2020-3 lead-free package. Each device will protect one line. The combination of small size, and high surge capability makes them ideal for use in applications such as cellular phones, LCD displays, USB, and multi media card interfaces.

Features

- 6800W peak pulse power (8/20 μs)
- Low leakage: nA level
- Operating voltage: 18V
- Ultra low clamping voltage
- One power line protects
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 Air discharge: $\pm 30\text{kV}$
 Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 165A (8/20 μs)
- RoHS Compliant

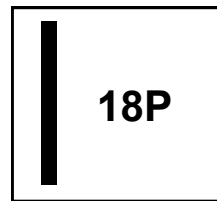
Mechanical Characteristics

- Package: DFN2020-3
- Case Material: "Green" Molding Compound
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

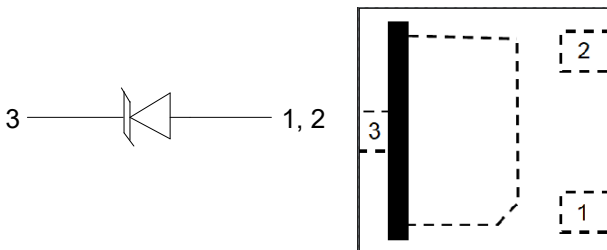
- Power Management
- Industrial Application
- Power Supply Protection

Marking Information



18P = Device Marking Code

Equivalent Circuit and Pin Configuration



Circuit and Pin Schematic

Ordering Information

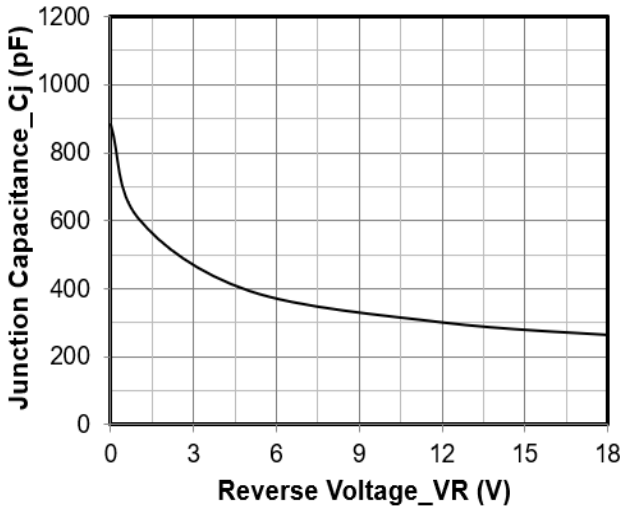
Part Number	Packaging	Reel Size
AU1801P4-3D	3000/Tape & Reel	7 inch

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise specified)

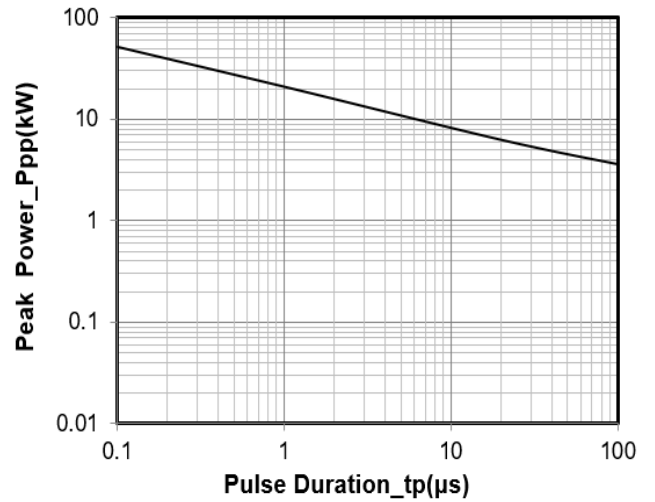
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	6270	W
Peak Pulse Current (8/20 μs)	I _{PP}	165	A
ESD per IEC 61000-4-2 (Air)	V _{ESD}	± 30	kV
ESD per IEC 61000-4-2 (Contact)		± 30	
Operating Temperature Range	T _J	-55 to +125	$^\circ\text{C}$
Storage Temperature Range	T _{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

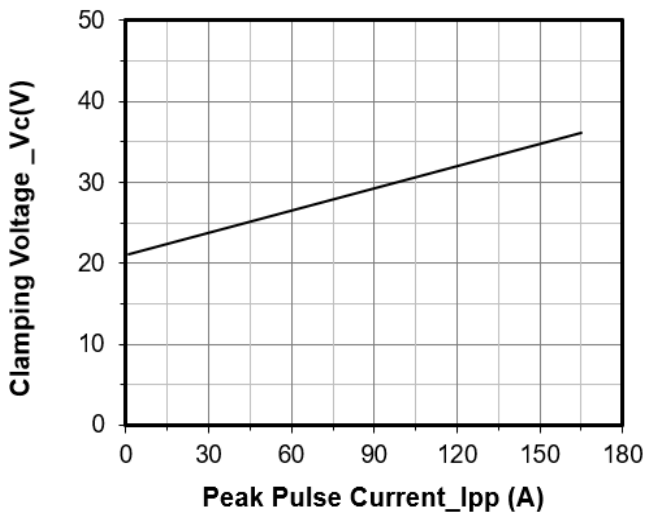
Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			18	V	
Breakdown Voltage	V _{BR}	19			V	I _T = 1mA
Reverse Leakage Current	I _R			0.5	μA	V _{RWM} = 18V
Clamping Voltage	V _C			25	V	I _{PP} = 20A (8 x 20 μs pulse)
Clamping Voltage	V _C			38	V	I _{PP} = 165A (8 x 20 μs pulse)
Junction Capacitance	C _J		900		pF	V _R = 0V, f = 1MHz



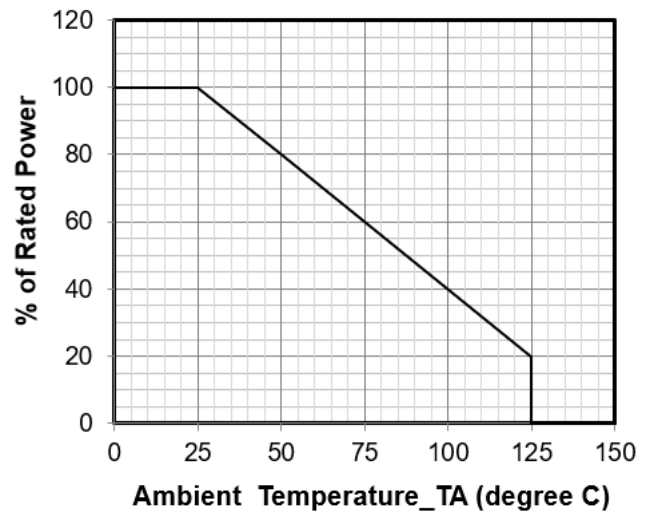
Junction Capacitance vs. Reverse Voltage



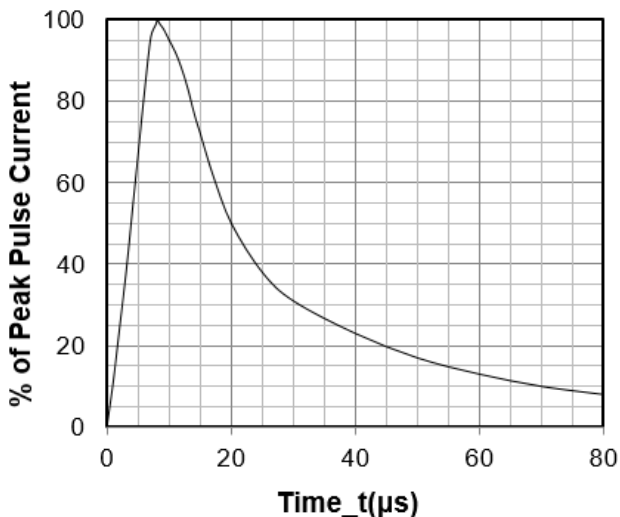
Peak Pulse Power vs. Pulse Time



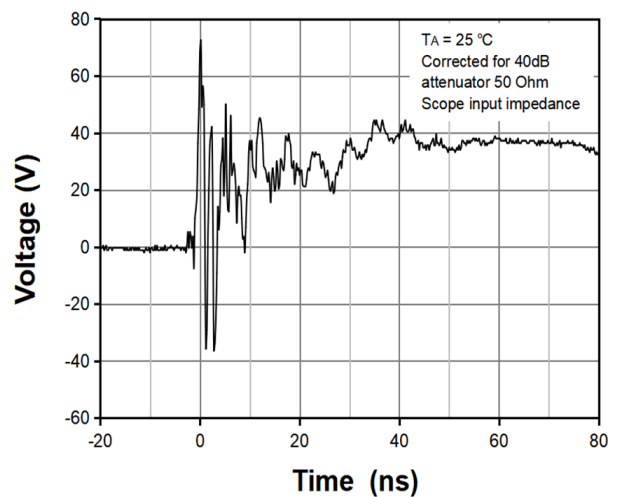
Clamping Voltage vs. Peak Pulse Current (tp = 8/20μs)



Power Derating Curve



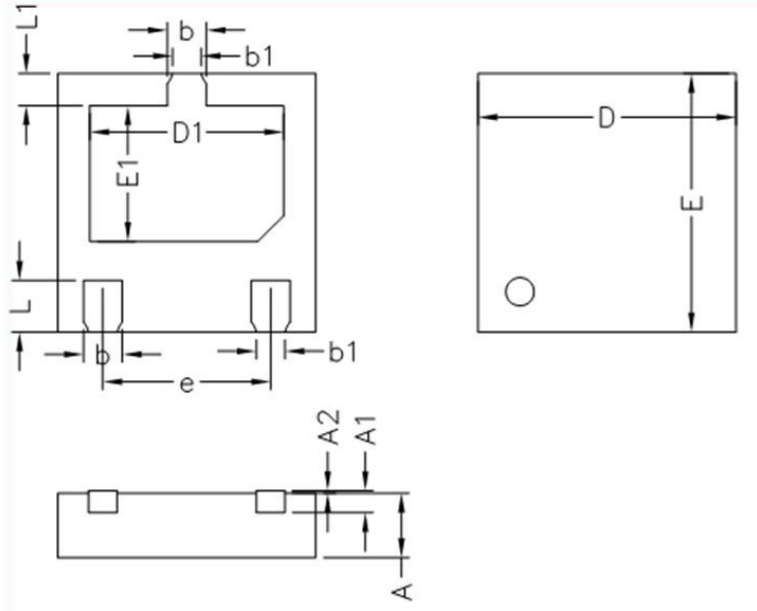
8 X 20μs Pulse Waveform



ESD Clamping Voltage

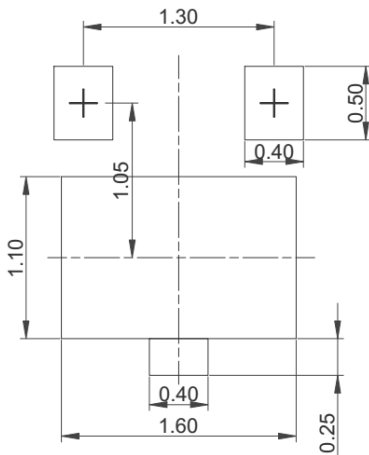
8 kV Contact per IEC61000-4-2

DFN2020-3 Package Outline Drawing



SYM	MILLIMETERS		
	MIN	NOM	MAX
A	0.45	0.50	0.60
A1	0.15REF		
A2	0.00	0.02	0.05
b	0.25	0.30	0.35
b1	0.22REF		
D	1.95	2.00	2.05
D1	1.45	1.50	1.55
E	1.95	2.00	2.05
E1	1.00	1.05	1.10
e	1.30BSC		
L	0.35	0.40	0.45
L1	0.20	0.25	0.30

Suggested Land Pattern



Unit: mm

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